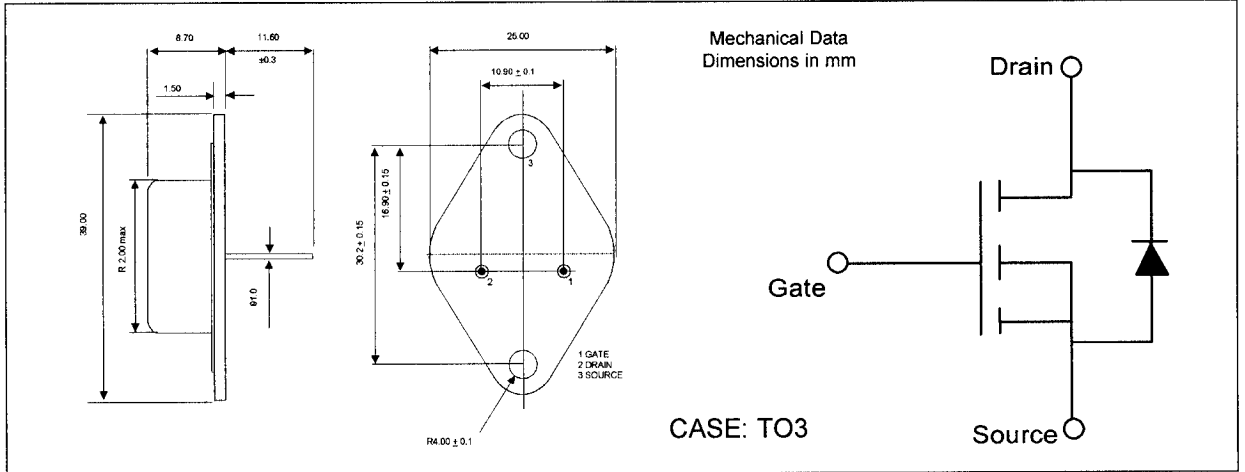


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ABSOLUTE MAXIMUM RATING (T case = 25 °C unless otherwise stated)		ECF10-25
V _{DSX}	Drain - Source Voltage	250V
V _{GSS}	Gate - Source Voltage	±14V
I _D	Continuous Drain Current	8A
I _{D(PK)}	Body Drain Diode	8A
P _D	Total Power Dissipation @ (T case = 25 °C)	125W
T _{stg}	Storage Temperature Range	-55 to 150 °C
T _j	Maximum Operating Junction Temperature	150 °C
RθJC	Thermal Resistance Junction - case	1.0 °C/W

STATIC CHARACTERISTICS (T case = 25 °C unless otherwise stated)

Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
BV _{DSX}	Drain - Source Breakdown Voltage V _{GS} = -10V	250			V
BV _{GSS}	Gate - Source Breakdown Voltage V _{DS} = 0 IG = ±100uA	±14			V
V _{GS(OFF)}	Gate-Source Cut-Off Voltage V _{DS} = 10V ID= 100mA	0.15		1.5	V
V _{DS(SAT)*}	Drain - Source Saturation Voltage V _{GD} = 0 ID = 8A			12	V
I _{DSX}	Drain - Source Cut - Off Current V _{GS} = -10V V _{DS} =250V			10	mA
Yfs*	Forward Transfer Admittance V _{DS} = 10V ID = 3A	0.7		2	S

DYNAMIC CHARACTERISTICS (T case = 25 °C unless otherwise stated)

Characteristic	Test Conditions	N-Channel	P-Channel	UNIT
C _{iss}	V _{DS} = ±10V f = 1 MHz			pF
C _{oss}				
C _{rss}				
t _{on}	V _{DS} = ±20V			ns
t _{off}	ID = ±5A			

*Pulse Test: Pulse width = 300uS, Duty Cycle ≤2%

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